

# Ren-Jie Chang

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

15  
papers

321  
citations

12  
h-index

15  
g-index

15  
ext. papers

418  
ext. citations

9.9  
avg, IF

3.47  
L-index

#	Paper	IF	Citations
15	GaS:WS Heterojunctions for Ultrathin Two-Dimensional Photodetectors with Large Linear Dynamic Range across Broad Wavelengths. <i>ACS Nano</i> , <b>2021</b> ,	16.7	7
14	Controlling Defects in Continuous 2D GaS Films for High-Performance Wavelength-Tunable UV-Discriminating Photodetectors. <i>Advanced Materials</i> , <b>2020</b> , 32, e1906958	24	24
13	High Photoresponsivity in Ultrathin 2D Lateral Graphene:WS:Graphene Photodetectors Using Direct CVD Growth. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2019</b> , 11, 6421-6430	9.5	52
12	Atomic structural catalogue of defects and vertical stacking in 2H/3R mixed polytype multilayer WS pyramids. <i>Nanoscale</i> , <b>2019</b> , 11, 10859-10871	7.7	2
11	High-Performance WS Monolayer Light-Emitting Tunneling Devices Using 2D Materials Grown by Chemical Vapor Deposition. <i>ACS Nano</i> , <b>2019</b> , 13, 4530-4537	16.7	34
10	Morphology Control of Two-Dimensional Tin Disulfide on Transition Metal Dichalcogenides Using Chemical Vapor Deposition for Nanoelectronic Applications. <i>ACS Applied Nano Materials</i> , <b>2019</b> , 2, 4222-4231	5.6	12
9	Postgrowth Substitutional Tin Doping of 2D WS Crystals Using Chemical Vapor Deposition. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2019</b> , 11, 24279-24288	9.5	13
8	Ultrathin All-2D Lateral Graphene/GaS/Graphene UV Photodetectors by Direct CVD Growth. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2019</b> , 11, 48172-48178	9.5	19
7	Self-Limiting Growth of High-Quality 2D Monolayer MoS <sub>2</sub> by Direct Sulfurization Using Precursor-Soluble Substrates for Advanced Field-Effect Transistors and Photodetectors. <i>ACS Applied Nano Materials</i> , <b>2019</b> , 2, 369-378	5.6	20
6	High-Performance All 2D-Layered Tin Disulfide: Graphene Photodetecting Transistors with Thickness-Controlled Interface Dynamics. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2018</b> , 10, 13002-13010	9.5	23
5	Chemical Vapor Deposition Growth of Two-Dimensional Monolayer Gallium Sulfide Crystals Using Hydrogen Reduction of GaS. <i>ACS Omega</i> , <b>2018</b> , 3, 7897-7903	3.9	24
4	2D-Layer-Dependent Behavior in Lateral Au/WS <sub>2</sub> /Graphene Photodiode Devices with Optical Modulation of Schottky Barriers. <i>ACS Applied Nano Materials</i> , <b>2018</b> , 1, 6874-6881	5.6	14
3	High-Performance Two-Dimensional Schottky Diodes Utilizing Chemical Vapour Deposition-Grown Graphene-MoS Heterojunctions. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2018</b> , 10, 37258-37266	9.5	17
2	Effects of surface oxidation of Cu substrates on the growth kinetics of graphene by chemical vapor deposition. <i>Nanoscale</i> , <b>2017</b> , 9, 2324-2329	7.7	14
1	Growth of Large Single-Crystalline Monolayer Hexagonal Boron Nitride by Oxide-Assisted Chemical Vapor Deposition. <i>Chemistry of Materials</i> , <b>2017</b> , 29, 6252-6260	9.6	46